

**Electrical Characteristics of the IGBT** $T_j = 25$ unless otherwise specified

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static						
Collector-Emitter Breakdown Voltage	BV_{CES}	$V_{GE}=0V, I_C=250\mu A$	650		-	V
Gate Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=1.20mA$	.25	3.75	4. 5	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE}=15V, I_C=100A$ $T_j=25^{\circ}C,$ $T_j=125^{\circ}C$ $T_j=150^{\circ}C$				

**Electrical Characteristics of the Diode** $T_j = 25$ unless otherwise specified

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
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Static



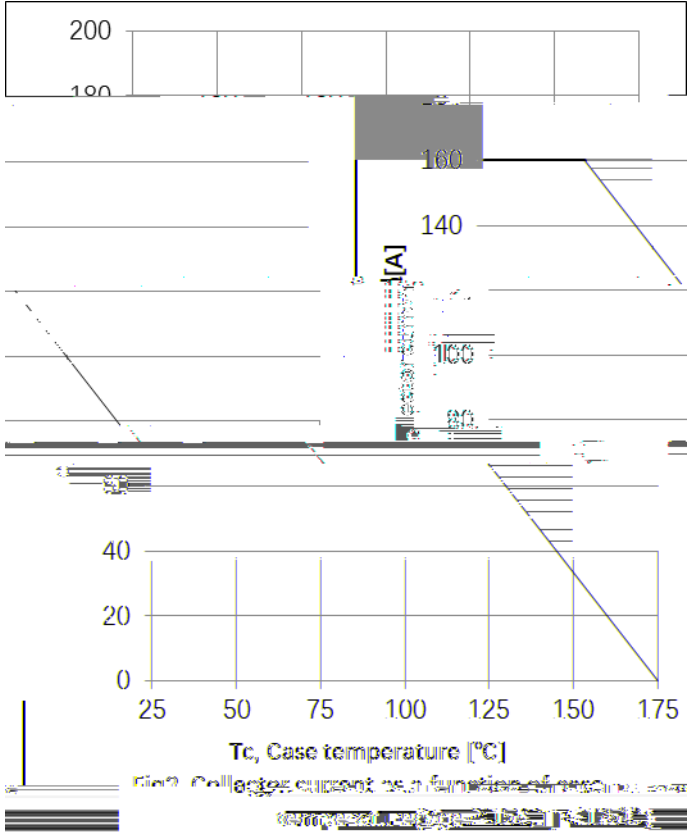
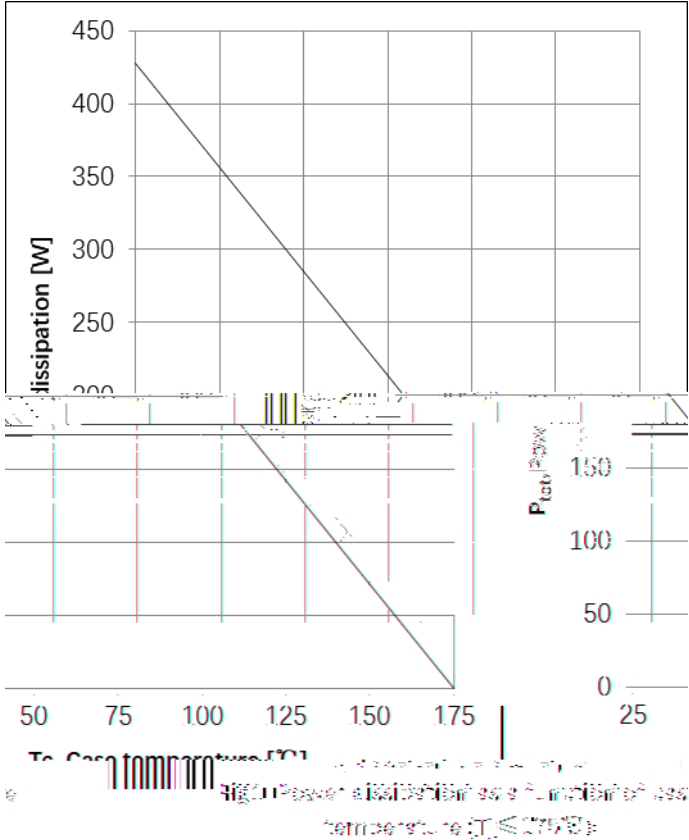
DGW100N65CTS1D

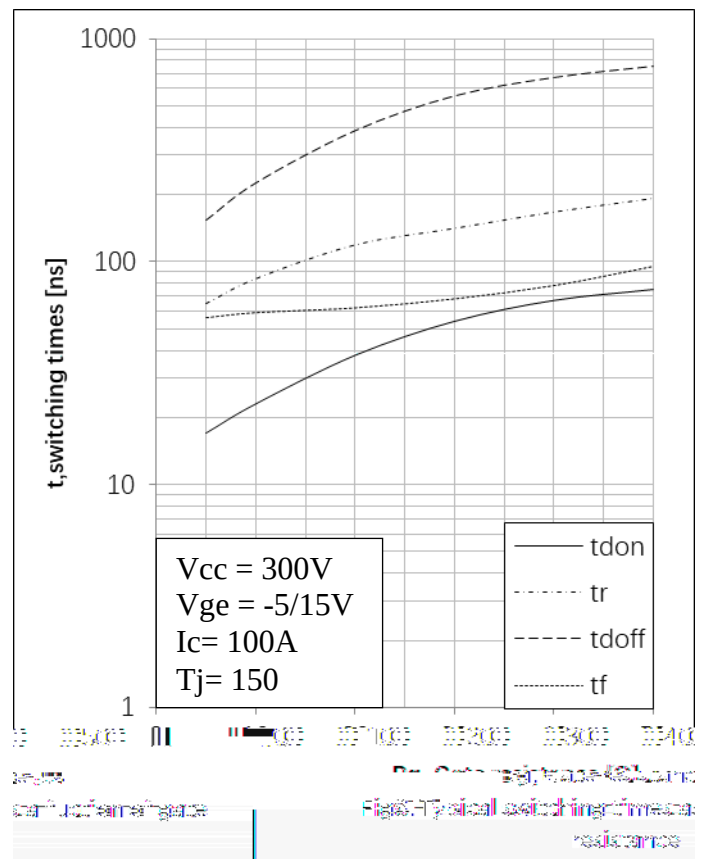
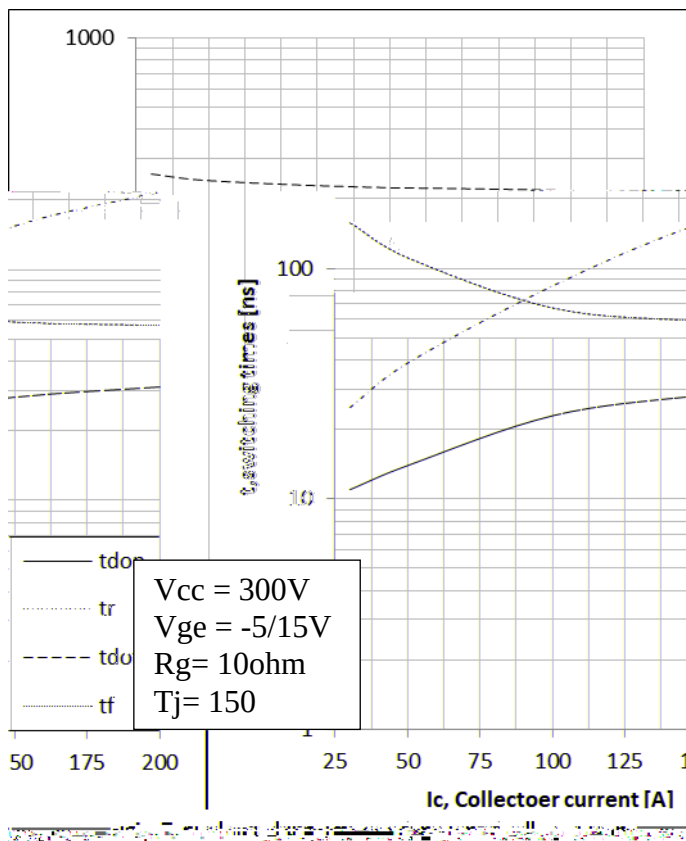
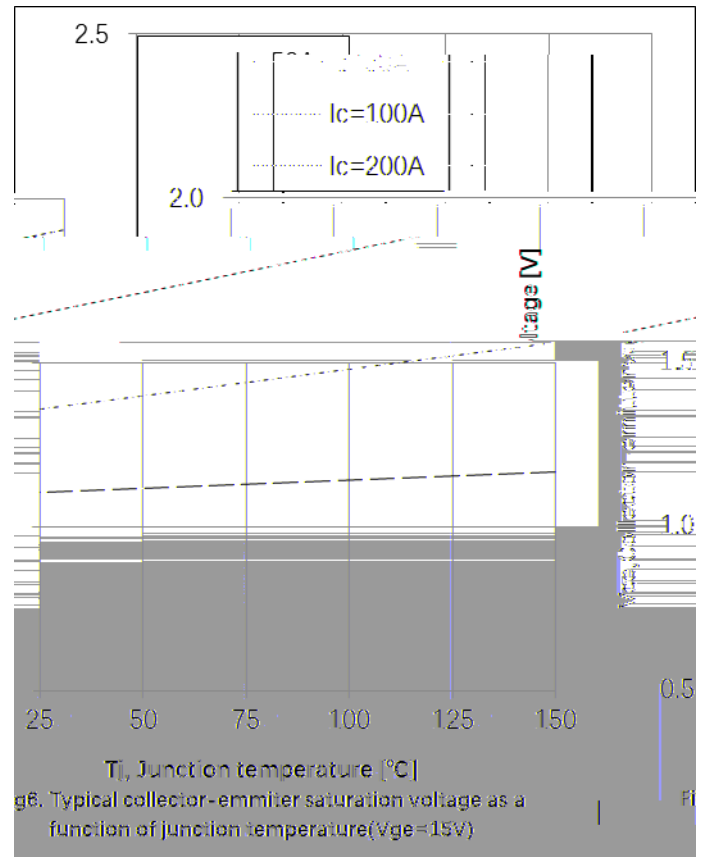
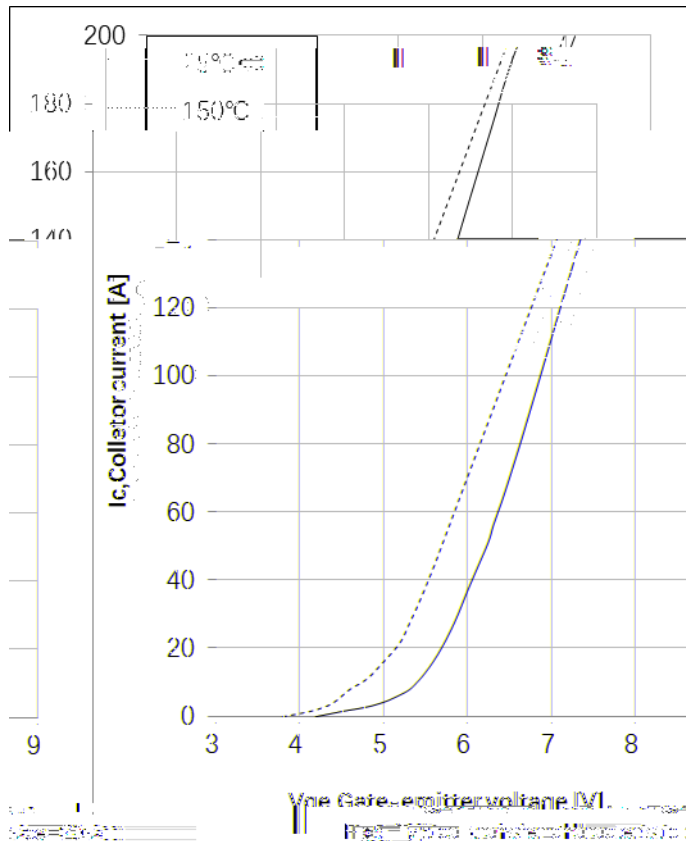
RoHS
COMPLIANT

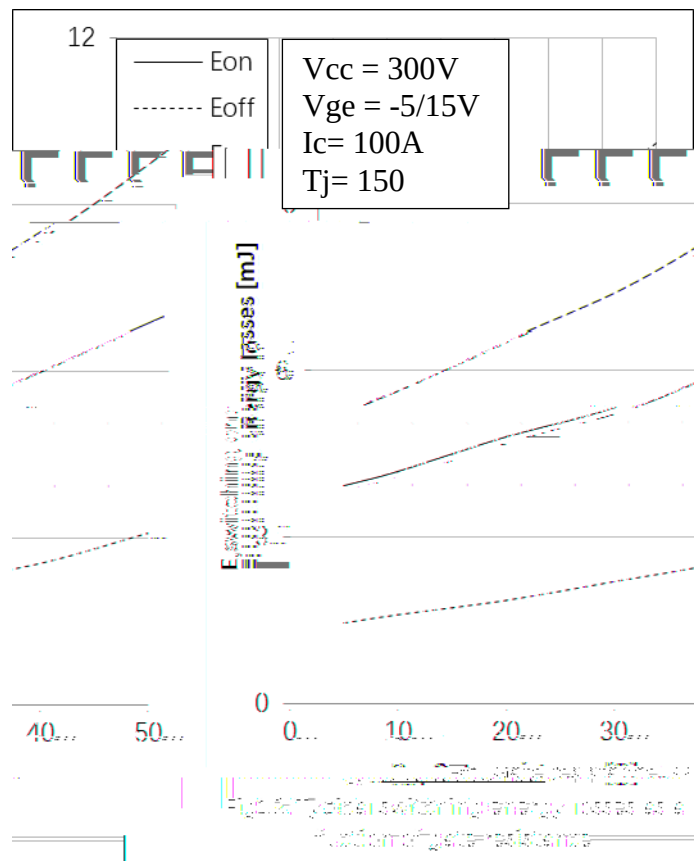
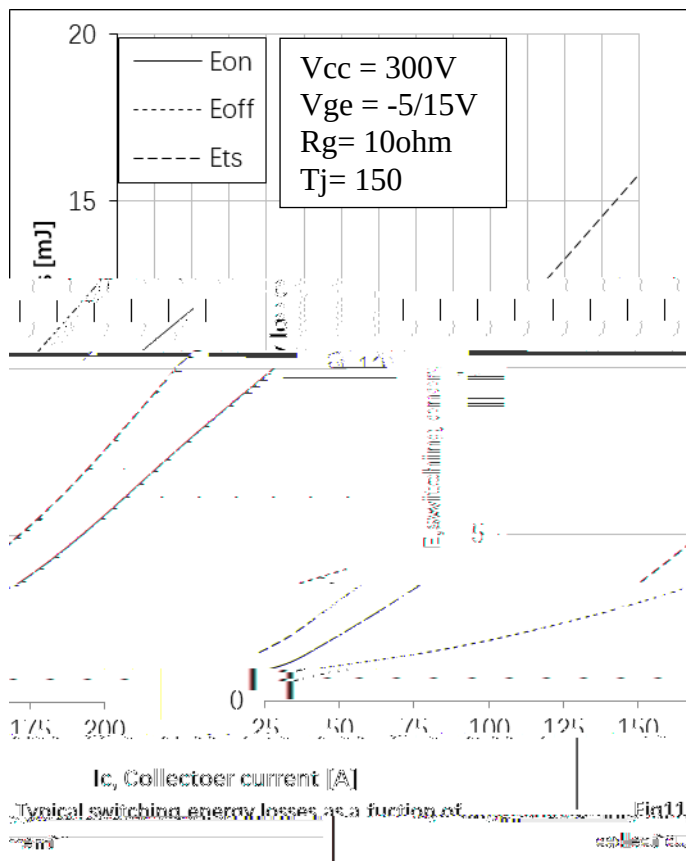
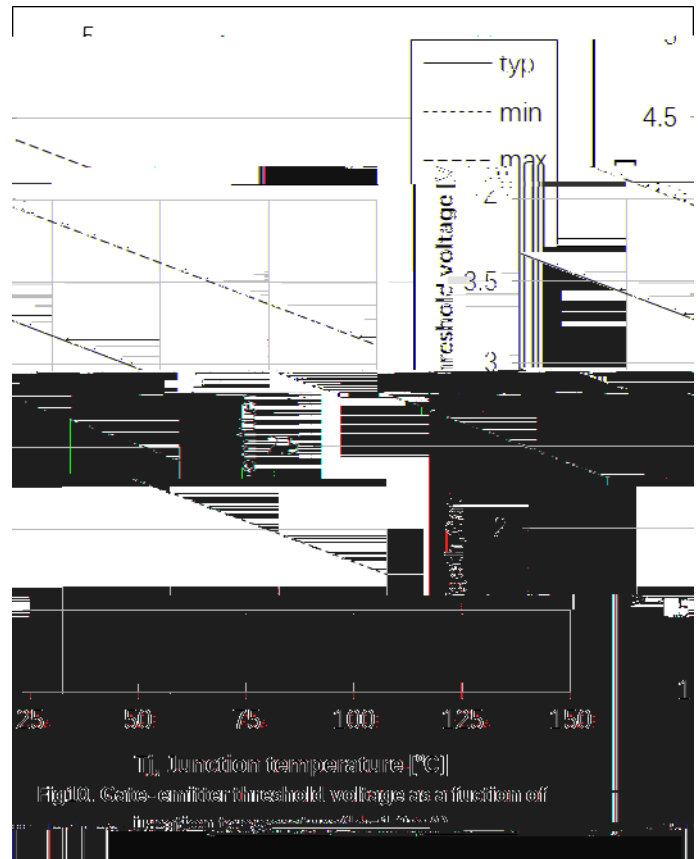
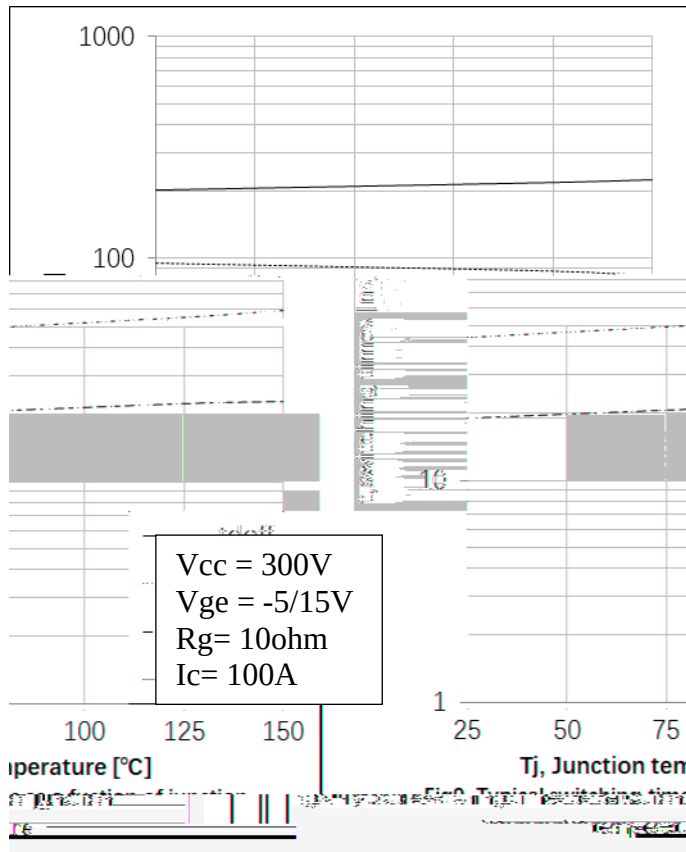


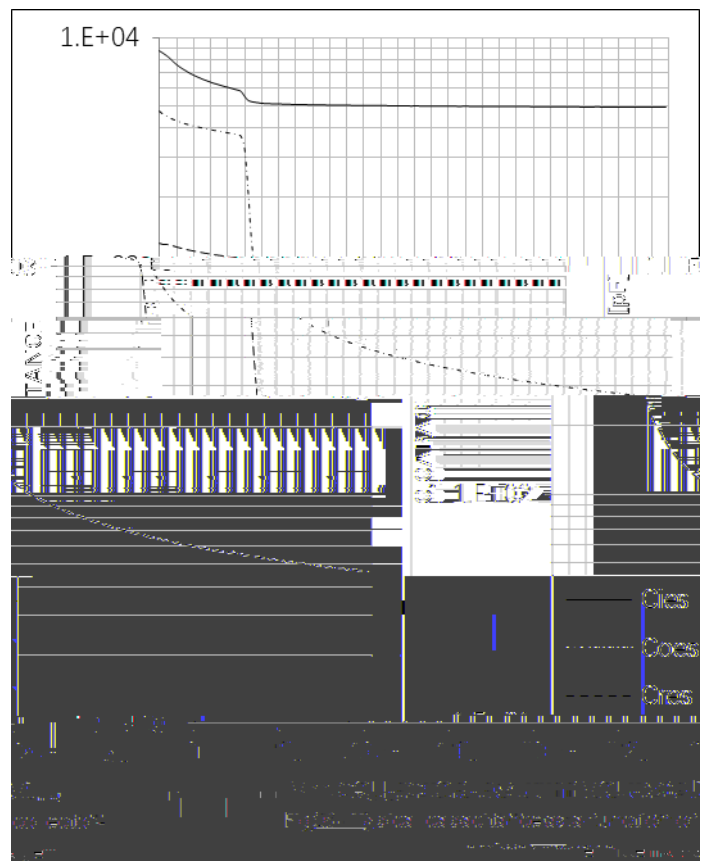
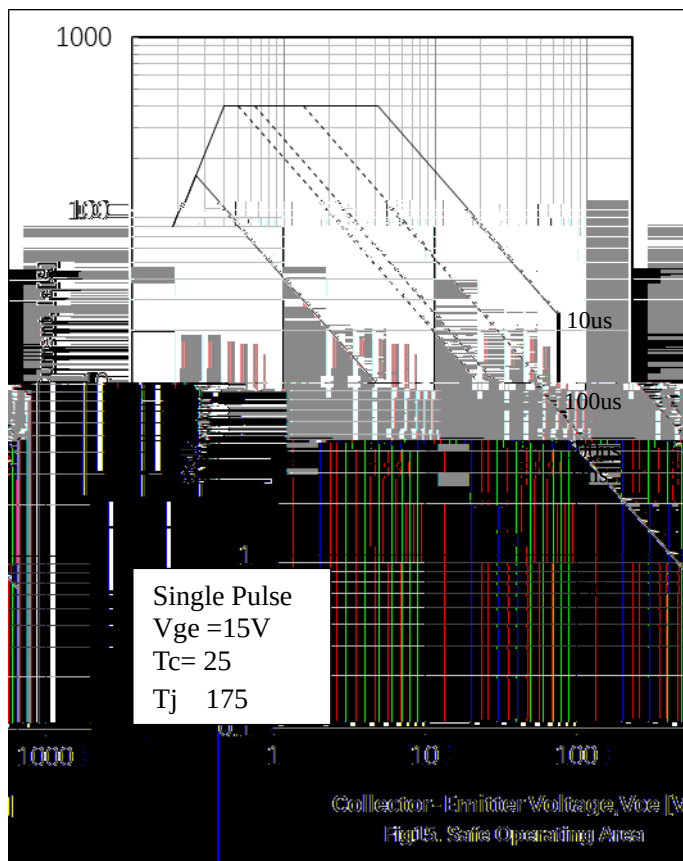
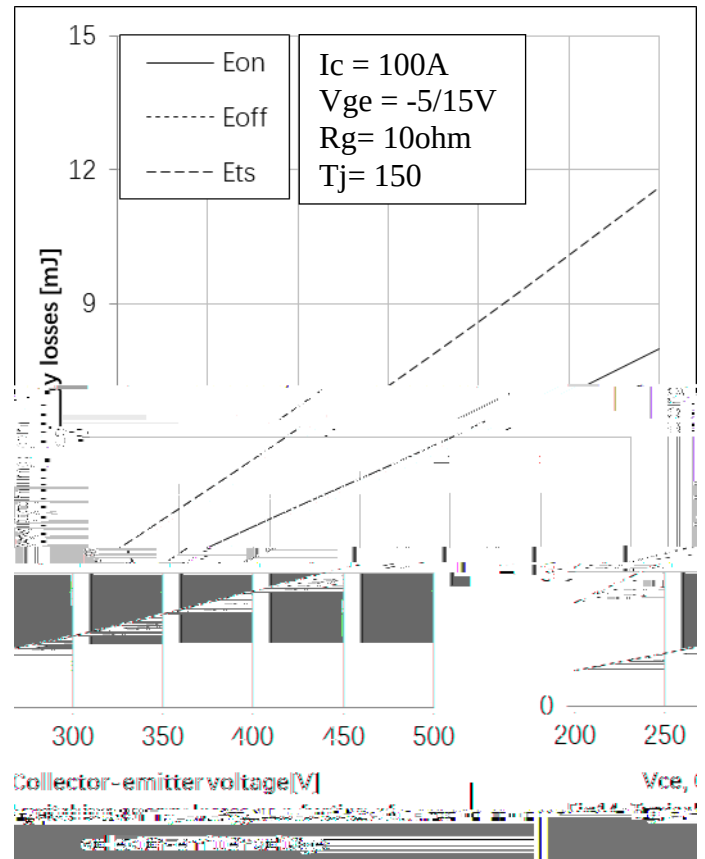
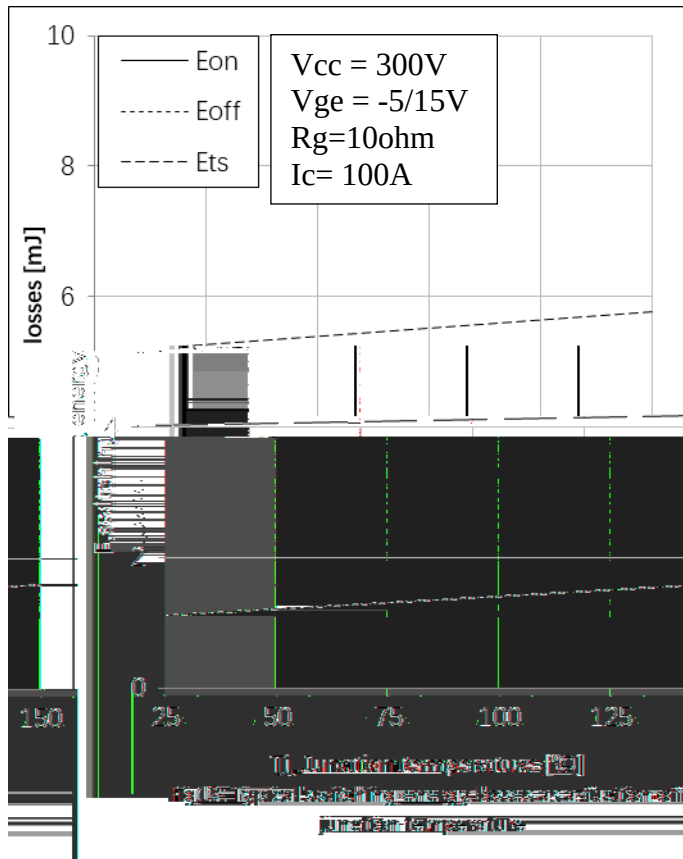
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RoHS
COMPLIANT









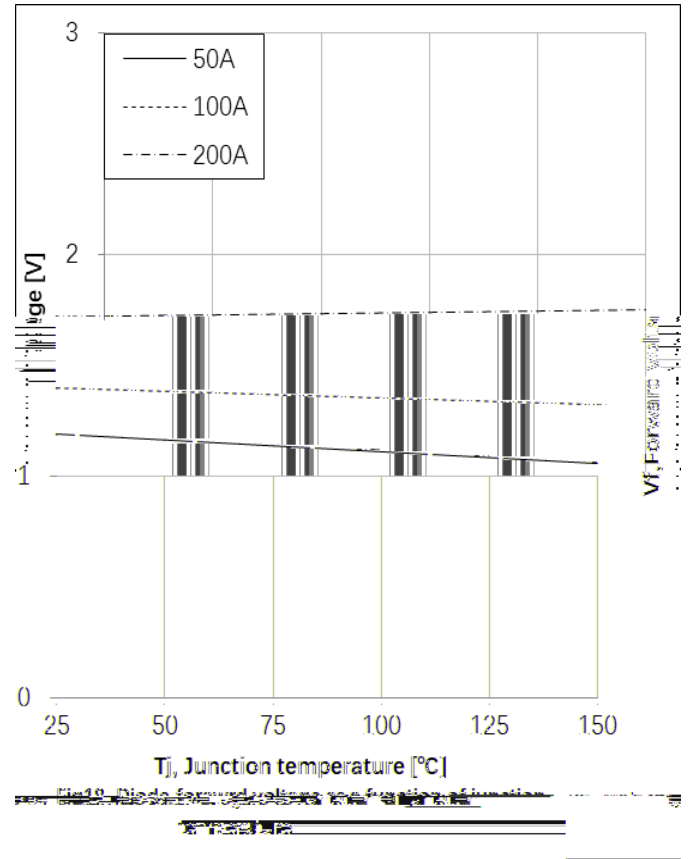
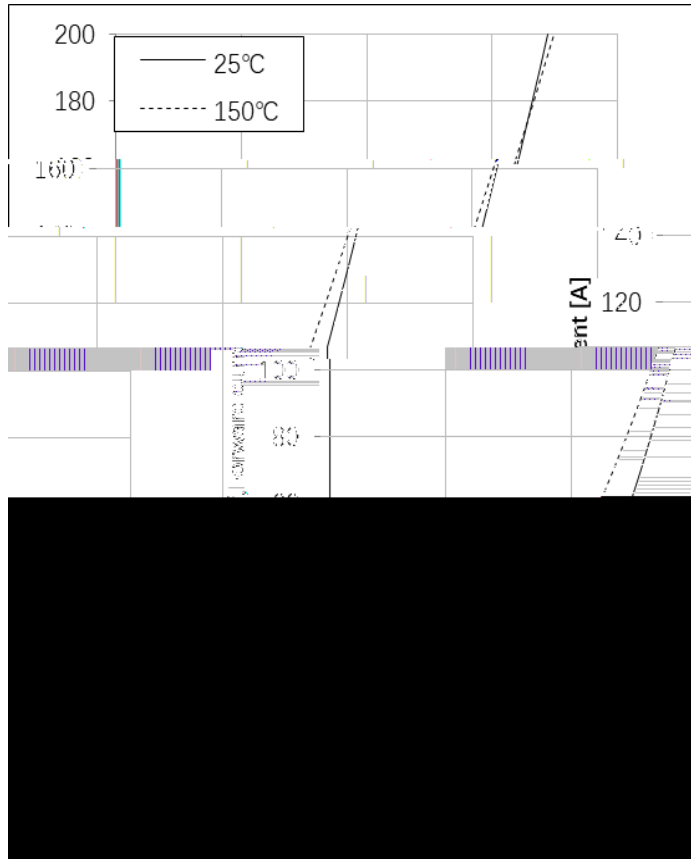
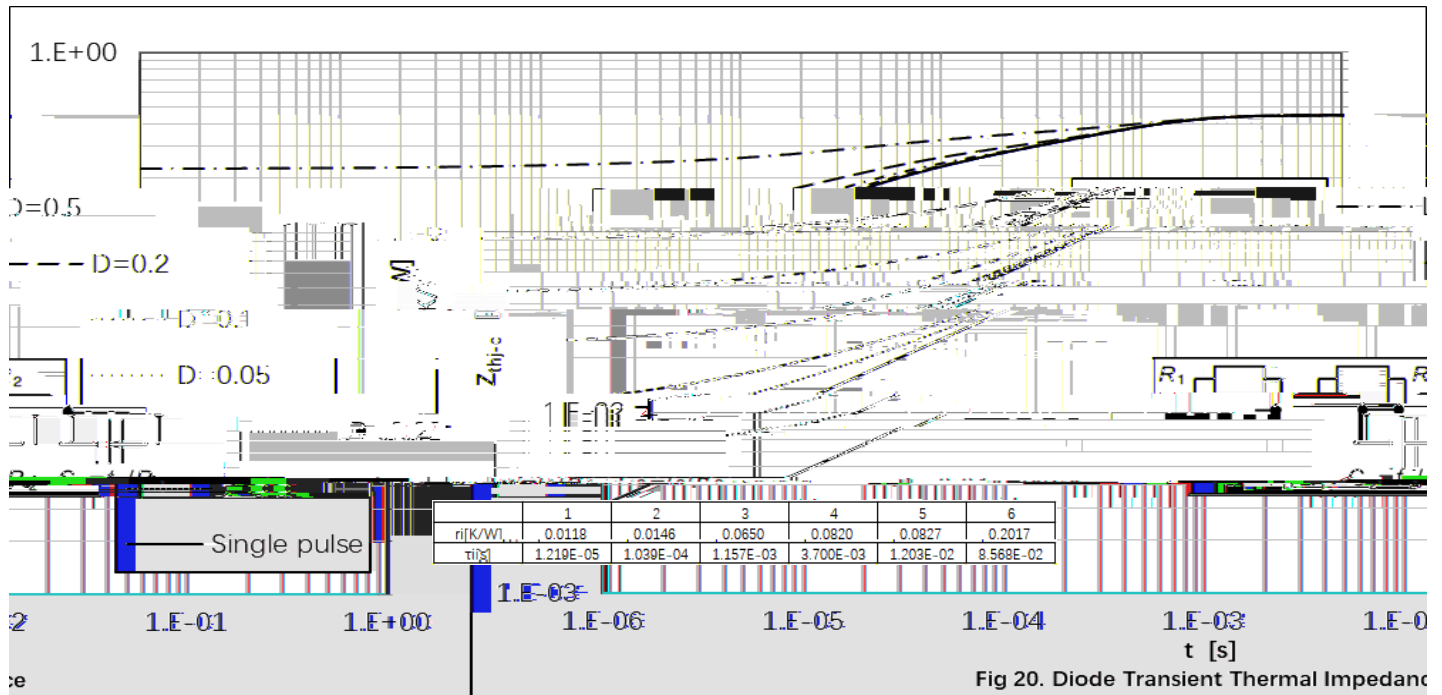
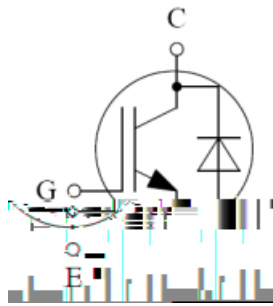


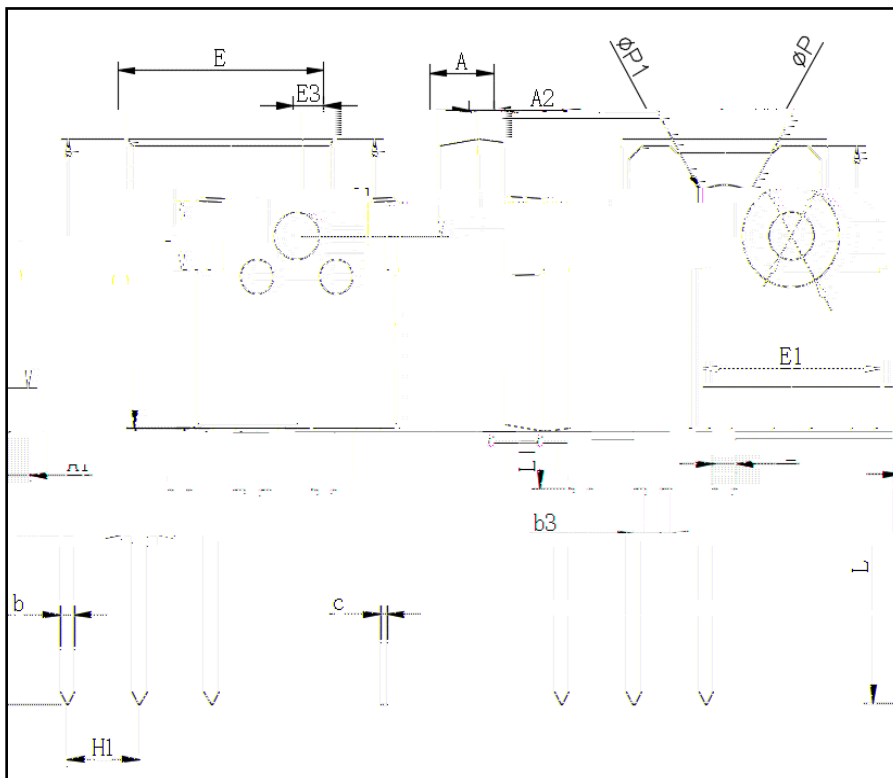
Fig 19. IGBT Transient Thermal Impedance





Package Outline Information

CASE: TO 247



TO-247AB		
Dim	Min	Max
A	4.80	5.20
A1	2.21	2.61
A2	1.85	2.15
b	1.0	1.4
b2	1.91	2.21
C	0.5	0.7
D	20.70	21.30
D1	16.25	16.85
E	15.50	16.10
E1	13.0	13.6
E2	4.80	5.20
E3	2.30	2.70
L	19.62	20.22
L1	-	4.30
ΦP	3.40	3.80
ΦP1	-	7.30
S	6.15TYP	
H1	5.44TYP	
b3	2.80	3.20